Characteristics of Li- doped Ni-Cobalt Oxide Thin Films Prepared by PLD Process

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Extended Abstract

Highly transparent p-type transparent oxide semiconductors are essential for transparent electronic devices. In this study Li doped NiCo₂O₄ spinel oxide thin films were fabricated for p type transparent oxide semiconductor by using pulsed laser deposition. Thin films with spinel phase were grown on glass and c-sapphire single crystal substrates at various substrate temperatures. The effects of doping concentrations, substrate temperatures and oxygen partial pressure on thin film structure, electrical and optical properties of the Li-doped (Ni,Co)Co₂O₄ spinel thin films were analyzed by XRD, Hall measurements, and UV spectrometer. Electrical conductivity and optical transmittance increased with increasing substrate temperature up to 400° C. The well crystallized spinel thin films of (111) preferred orientation were grown on the sapphire substrate above 200° C. Oxygen partial pressure was critical processing factor for spinel phase formation as well as optical transmittance and electrical conductivity. When oxygen partial pressures was lower than 5mtorr, rock salt type (Ni,Co)O phases were more favourable and electrical conductivity decreased very sharply. Li doped (Ni,Co)Co₂O₄ spinel thin films with electrical conductivity of 30 S/cm and optical transmittance about 60% were fabricated with optimum processing parameters. In this study, the influences of various processing parameters on the characteristics of Li doped (Ni,Co)Co₂O₄ spinel thin films were discussed.

Facchetti, A. (2009). Transparent Electronics, Wiley.